## **RSC** Advances



View Article Online

## CORRECTION

Check for updates

Cite this: RSC Adv., 2023, 13, 14472

## Correction: Controlling barrier height and spectral responsivity of p-i-n based GeSn photodetectors *via* arsenic incorporation

Mohamed A. Nawwar,<sup>\*a</sup> Magdy S. Abo Ghazala,<sup>a</sup> Lobna M. Sharaf El-Deen,<sup>a</sup> Badawi Anis,<sup>b</sup> Abdelhamid El-Shaer,<sup>c</sup> Ahmed Mourtada Elseman,<sup>d</sup> Mohamed M. Rashad<sup>d</sup> and Abd El-hady B. Kashyout<sup>\*e</sup>

DOI: 10.1039/d3ra90040a

rsc.li/rsc-advances

Correction for 'Controlling barrier height and spectral responsivity of p-i-n based GeSn photodetectors *via* arsenic incorporation' by Mohamed A. Nawwar *et al.*, *RSC Adv.*, 2023, **13**, 9154–9167, https://doi.org/10.1039/D3RA00805C.

The authors regret that the author associations with affiliations were incorrectly shown in the original manuscript. The corrected list of affiliations is as shown above.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

<sup>a</sup>Physics Department, Faculty of Science, Menoufia University, Menoufia, Shebin El-Koom, 32511, Egypt. E-mail: mohamed.nawwar@science.menofia.edu.eg <sup>b</sup>Spectroscopy Department, Physics Research Institute, National Research Centre, 33 El Bohouth St., Dokki, Giza, 12622, Egypt <sup>c</sup>Physics Department, Faculty of Science, Kafrelsheikh University, KafrelSheikh, 33516, Egypt

<sup>d</sup>Electronic & Magnetic Materials Department, Advanced Materials Institute, Central Metallurgical Research & Development Institute (CMRDI), Helwan-Cairo, 11421, Egypt <sup>s</sup>Electronic Materials Department, Advanced Technology and New Materials Research Institute, City of Scientific Research and Technological Applications (SRTA-City), New Borg El-Arab City, Alexandria, 21943, Egypt. E-mail: akashyout@srtacity.sci.eg